
Contents

About the Author	xvii
Preface	xix
Acknowledgements	xxi
Chapter 1 CMOS Latchup	1
1.1 CMOS Latchup	1
1.1.1 CMOS Latchup–What is Latchup?	1
1.1.2 CMOS Latchup–Why is Latchup Still an Issue?	5
1.1.3 Early CMOS Latchup History	6
1.2 Fundamental Concepts of Latchup Design Practice	10
1.3 Building a CMOS Latchup Strategy	14
1.3.1 Building a CMOS Business Strategy – 18 Steps in Building a CMOS Latchup Business Strategy	15
1.3.2 Building a CMOS Latchup Technology Strategy – 18 Steps in Building a CMOS Latchup Technology Strategy	15
1.4 CMOS Latchup Technology Migration Strategy	16
1.5 Key Metrics of Latchup Design Practice	18
1.6 CMOS Latchup Technology Trends and Scaling	19
1.7 Key Developments	21
1.7.1 Key Innovations	21
1.7.2 Key Contributions	21
1.7.3 Key Patents	25
1.8 Latchup Failure Mechanisms	25
1.9 CMOS Latchup Events	28
1.9.1 Power-Up Sequence Initiated Latchup	29
1.9.2 Input Pin Overshoot and Power-Up Sequence Initiated Latchup	29
1.9.3 Input Pin Undershoot and Power-Up Sequence Initiated Latchup	30
1.9.4 Multiple Power Supply Power-Up Sequence Initiated Latchup	30
1.9.5 Power Supply Overshoot Initiated Latchup	31
1.9.6 Power Supply Undershoot Initiated Latchup	32
1.9.7 Power Supply (Ground Rail) Undershoot Initiated Latchup	32
1.10 Electrostatic Discharge Sources	33
1.10.1 Human Body Model ESD Event	33

viii CONTENTS

1.10.2	Machine Model ESD Event	34
1.10.3	Cable Discharge Event Source	34
1.11	Single Event Latchup	36
1.11.1	High-Energy Photon Emissions	36
1.11.2	Alpha Particle Ionizing Source	37
1.11.3	Cosmic Ray Source	39
1.11.4	Heavy Ion Source	42
1.12	Summary and Closing Comments	44
	Problems	44
	References	46
Chapter 2 Bipolar Transistors		55
2.1	The Bipolar Transistor and CMOS Latchup	55
2.1.1	Fundamental Equations of Semiconductors and the Drift–Diffusion Current Constitutive Relationships	55
2.1.2	Diode Forward Bias Conditions	56
2.1.3	Diode Forward Bias Conditions and High-level Injection	57
2.2	Bipolar Transistor	60
2.2.1	Bipolar Current Gain	60
2.2.2	Bipolar Collector-to-Emitter Transport Factor	60
2.2.3	Bipolar Current Characteristics	62
2.2.4	Bipolar Model Gummel Plot	64
2.2.5	Bipolar Current Model–Ebers–Moll Model	64
2.2.6	Bipolar Transistor Base Defect	67
2.2.7	Bipolar Transistor Emitter Defect	69
2.2.8	Bipolar Base Current–Base Defect and Emitter Defect Relation to Bipolar Current Gain	71
2.3	Recombination Mechanisms	72
2.3.1	Shockley–Read–Hall (SRH) Generation–Recombination Model	73
2.3.2	Auger Recombination Model	74
2.3.3	Surface Recombination Mechanisms	76
2.3.4	Surface Recombination Velocity	76
2.3.5	Recombination Mechanisms and Neutron Irradiation	76
2.3.6	Recombination Mechanisms and Gold Recombination Centers	78
2.4	Photon Currents in Metallurgical Junctions	79
2.5	Avalanche Breakdown	81
2.5.1	Bipolar Transistor Breakdown	81
2.5.2	MOSFET Avalanche Breakdown	81
2.6	Vertical Bipolar Transistor Model	83
2.7	Lateral Bipolar Transistor Models	85
2.7.1	Lindmayer–Schneider Model	86
2.7.2	Bipolar Current Gain with Lateral and Vertical Contributions	87
2.7.3	Lateral Bipolar Transistor Models – Nonfield-Assisted	89
2.7.4	Lateral Bipolar Transistor Models – Nonfield-Assisted Base Transport Factor	90
2.8	Lateral Bipolar Transistor Models with Electric Field Assist	91
2.8.1	Lateral Bipolar Transistor Models – Base Transport Factor with Electric Field Assisted Base Transport	93

2.8.2	Lateral Bipolar Transistor Models – Bipolar Current Gain with Electric Field Assisted Base Transport	94
2.8.3	Lateral Bipolar Transistor Models – Two-Dimensional Hole Current Analysis with Electric Field Assist	94
2.8.4	Lateral Bipolar Transistor Models – Vertical Hole Current with Lateral Electric Field Assist	96
2.9	Lateral Bipolar Transistor Models–Nonuniform Vertical Profile	97
2.9.1	Lateral Bipolar Transistor Models–Gunn, Dutton, and Whittier n–/n+ Step Junction Model	98
2.9.2	Lateral Bipolar Transistor Models – Bipolar Current Gain with Nonuniform Vertical Profile	100
2.9.3	Lateral Bipolar Transistor Models – Base Effective Diffusion Length	101
2.10	Triple-Well Bipolar Transistor Models – Lateral and Vertical Contributions	106
2.11	Merged Triple-Well Bipolar Models	108
2.11.1	Merged Triple-Well Models – Lateral and Vertical Contributions with Buried Layer	108
2.11.2	Merged Triple-Well Models – Lateral and Vertical Contributions	110
2.11.3	The Lateral Bipolar Transistor – Substrate Spreading Resistance Representation (Estreich)	111
2.11.4	The Lateral Bipolar Transistor – Substrate Transmission Line Representation (Troutman and Hargrove)	112
2.11.5	The Lateral Bipolar Transistor – Substrate Lossy Transmission Line Representation (Troutman and Hargrove)	115
2.11.6	The Bipolar Transistor – Substrate Transfer Resistance Representation	117
2.12	Summary and Closing Comments	120
	Problems	121
	References	122
Chapter 3 Latchup Theory		125
3.1	Regenerative Feedback	125
3.1.1	Regenerative Feedback without Shunt Resistors and Alpha Representation	126
3.1.2	Regenerative Feedback without Shunt Resistors and Beta Representation	128
3.1.3	Regenerative Feedback with Shunt Resistors and Alpha Representation	128
3.1.4	Regenerative Feedback with Shunt Resistors and Beta Representation	129
3.1.5	Sensitivity Factors – Beta Product	131
3.2	Latchup Criterion with Emitter Resistance	132
3.3	Holding Point Conditions	135
3.3.1	Holding Voltage	135
3.3.2	Holding Current	135
3.3.3	Holding Current Contours	136
3.3.4	Sensitivity Factors – Holding Current	137
3.4	Resistance Space	138
3.4.1	Resistance Space – Constant Holding Condition Contours	139
3.4.2	Resistance Space Plots	141
3.5	Beta Space	142
3.6	CMOS Latchup Differential Tetrode Condition	142
3.6.1	CMOS Latchup Differential Tetrode Condition – First Representation	144

x CONTENTS

3.6.2	CMOS Latchup Differential Tetrode Condition – Second Representation	145
3.6.3	CMOS Latchup Differential Tetrode Condition – Third Representation	147
3.7	CMOS Latchup Differential Holding Current Relationship	151
3.8	CMOS Latchup Differential Holding Voltage Relationship	152
3.9	CMOS Latchup Differential Resistance Relationship	153
3.10	Differential Generalized Alpha Space Relationship	154
3.11	High-Level Injection	156
3.11.1	High-Level Injection – Base Width Modulation	156
3.11.2	High-Level Injection – Knee and Base Width Modulation Correction	157
3.11.3	High-Level Injection – CMOS Latchup Differential Tetrode Condition	157
3.12	Transient Latchup	160
3.12.1	Transient Latchup – The Four States	160
3.12.2	Transient Latchup – Generalized Excitation Differential Equation and Analysis of the Four States	161
3.12.3	Transient Latchup – Power-Up Excitation	164
3.13	External Latchup	168
3.13.1	External Latchup Diode Injection Source Analysis	168
3.13.2	External Latchup Criterion	170
3.13.3	External Latchup Propagation	173
3.14	Alpha Particle Induced Latchup	178
3.14.1	Charge Collection Process and Analysis	179
3.14.2	Circuit Analysis and Monte Carlo Simulation	181
3.14.3	Maximum Collection Evaluation in a Parallelepiped Region	182
3.15	Summary and Closing Comments	183
	Problems	183
	References	184

Chapter 4 Latchup Structures, Characterization and Test 189

4.1	Guard Rings	189
4.1.1	Intradevice Integrated Guard Ring	191
4.1.2	Intracircuit Guard Ring	191
4.1.3	Intercircuit Guard Ring	192
4.1.4	Interchip Sector Guard Ring	192
4.1.5	ESD Guard Rings – Usage of Guard Rings in ESD Protection	192
4.2	Latchup Characterization Structures – Single- and Dual-Well CMOS PNP	192
	Test Structures	192
4.2.1	Basic pnpn Structure with Single Substrate Contact Spacing	193
4.2.2	Basic pnpn Structure with Internal Well Guard Ring Structure	194
4.2.3	Basic pnpn Structure with Internal Substrate Guard Rings	196
4.2.4	Basic pnpn Structure with Internal Well Guard Ring and Substrate Guard Ring	197
4.2.5	Basic pnpn Structure with Multiple p+/n+ Spacings	199
4.2.6	Basic pnpn Structure with Multiple Well and Substrate Contact Spacings	199
4.2.7	Basic pnpn with Large Substrate Resistance Measurements	200
4.2.8	Basic pnpn with External Injection Source	201
4.3	Latchup Characterization – Basic Triple-Well pnpn Latchup Test Structures	205
4.4	Latchup Characterization Techniques – pnpn Structures with Deep Trench	206

4.5	Latchup Characterization and Testing – Nonautomated Test Systems and Methodology	209
4.5.1	Latchup Testing – dc Test Methods	210
4.5.2	Latchup Testing – Pulsed ac Latchup Test Systems and Methodology	211
4.6	Latchup Characterization and Testing – Automatic Test Systems	213
4.6.1	Noncommercial Wafer-level Automatic Test Systems	213
4.6.2	Commercial Automated Product Test System	214
4.7	Latchup Characterization – Wafer-Level Test Procedures	217
4.7.1	Latchup Characterization Test – Ramped Power Supply Voltage Study	217
4.7.2	Latchup Characterization Test – p+ Anode Power Supply Overshoot Study	218
4.7.3	Latchup Characterization Test – Ramped Negative Power Supply Voltage Study	219
4.7.4	Latchup Characterization Test – n+ Cathode Ground Power Supply Undershoot Study	220
4.8	Latchup Characterization Techniques – Wafer-level Transmission Line Pulse Methodology	221
4.9	Latchup Characterization – Transient Latchup	223
4.9.1	Latchup Characterization – Wafer-level Transient Latchup	224
4.9.2	Latchup Characterization – Transient Latchup (TLU) Amplifier Product-level Test	226
4.10	Guard Ring Characterization	230
4.10.1	Guard Ring Efficiency	231
4.10.2	Guard Ring Theory – A Generalized Bipolar Transistor Perspective	232
4.10.3	Guard Ring Theory – A Probability of Escape Perspective	233
4.10.4	Guard Ring Characterization – Electrical Measurements	234
4.11	Latchup Failure Analysis Techniques	236
4.11.1	Failure Analysis – Optical Microscope	237
4.11.2	Failure Analysis – Emission Microscope (EMMI) Tool	238
4.11.3	Failure Analysis Technique – EMMI Tool Stellari Animation Methodology	240
4.11.4	Failure Analysis Technique – Scanning Superconducting Quantum Interference Device (SQUID)	242
4.11.5	Failure Analysis Techniques – Modified Picosecond Imaging Circuit Analysis Tool – the TLP-PICA Methodology	243
4.11.6	Failure Analysis – Thermal Imaging Techniques	250
4.12	Summary and Closing Comments	250
	Problems	251
	References	253

Chapter 5 CMOS Latchup Process Features and Solutions – Dual-Well and Triple-Well CMOS	257
5.1 CMOS Semiconductor Process Solutions and CMOS Latchup	257
5.2 Substrates	257
5.2.1 Epitaxial Thickness	259

xii CONTENTS

5.3	n-Wells	261
5.3.1	Diffused n-Well Design	261
5.3.2	Retrograde n-Well Design	263
5.3.3	Retrograde n-Well Design and Design Point Optimization	266
5.3.4	Retrograde n-Well Design for Latchup and ESD Design Synthesis	267
5.3.5	n-Wells: n-Well to Substrate Modulation	267
5.3.6	n-Well Depth Scaling	269
5.4	p-Well	269
5.4.1	p-Well Design and Design Point Synthesis	269
5.4.2	p-Well and p++ Substrates	269
5.4.3	p-Well Connecting Implants (Epitaxial Buried Implants)	270
5.5	p+/n+ Scaling	273
5.6	Isolation and Latchup	273
5.6.1	Recess Oxide (ROX) and LOCOS Isolation	274
5.6.2	Shallow Trench Isolation (STI)	275
5.7	Silicide	277
5.8	Triple Well	277
5.8.1	Triple Well–Separate Wells	278
5.8.2	Decoupling of pnp and npn by Spatial Separation	278
5.8.3	Merged Triple-Well CMOS	279
5.8.4	Merged Triple Well with Blanket Implant	288
5.9	High-Dose Buried Layer	289
5.9.1	Buried Implanted Layer for Lateral Isolation (BILLI) Structure	289
5.9.2	Continuous High-Dose Buried Layer	290
5.9.3	HDBL Characterization	292
5.9.4	HDBL Recombination Time and Resistance Measurements	292
5.9.5	HDBL and Reachthrough Implant	293
5.10	Future Concepts	295
5.11	Summary and Closing Comments	295
	Problems	296
	References	296
Chapter 6 CMOS Latchup Process Features and Solutions – Bipolar and BiCMOS Technology		301
6.1	CMOS Latchup in Bipolar and RF BiCMOS Technology	301
6.2	Substrates – High-Resistance Substrates	301
6.2.1	Fifty Ohm Centimeter Substrate Resistance	306
6.2.2	Ultrahigh Substrate Resistance	310
6.3	Subcollectors	312
6.3.1	Subcollector – npn and pnp Bipolar Current Gain	313
6.3.2	Subcollector – β Product $\beta_{pnp}\beta_{nnp}$	315
6.3.3	Subcollector – Overshoot and Undershoot Currents	315
6.4	Alternative Isolation Concepts	317
6.5	Trench Isolation (TI)	317
6.5.1	Trench Isolation and Latchup	318
6.5.2	Trench Isolation and Subcollector	323
6.6	Deep Trench	328
6.6.1	Deep Trench as a Guard Ring	329

6.6.2	Deep Trench Guard Ring Characterization – Guard Ring Efficiency Methodology	329
6.6.3	Deep Trench Guard Ring Characterization – Bipolar Transistor Methodology	333
6.6.4	Deep Trench Structure Within the pnpn Structure	334
6.6.5	Deep Trench Structure and Subcollector	340
6.6.6	Electrically Connected Deep Trench Structure	343
6.7	Triple-Well and BiCMOS Processes Integration	346
6.7.1	Triple Well – Deep Trench and Triple Well Integration	347
6.7.2	Triple Well – Deep Trench and Subcollector	348
6.8	Heavily Doped Buried Layer Implant and BiCMOS Technology	351
6.9	Summary and Closing Comments	352
	Problems	352
	References	353
Chapter 7 CMOS Latchup – Circuits		357
7.1	Table of Circuit Interactions	357
7.2	Intrabook Latchup Mechanisms	359
7.2.1	CMOS Latchup Within an ESD Input Network	359
7.2.2	Intrabook Latchup Mechanisms – ESD Input Circuit and I/O Circuit Latchup	361
7.3	Interbook Latchup Mechanisms	362
7.3.1	Interbook Latchup Mechanisms – ESD Input Circuit and Power Clamp Latchup	362
7.3.2	Interbook Latchup Mechanisms – ESD Input Circuit and Power Clamp Latchup (Hsu <i>et al.</i>)	362
7.3.3	Interbook Latchup Mechanisms – I/O to ESD Power Clamps (Huh <i>et al.</i>)	365
7.3.4	Interbook Latchup Mechanisms – Power Supply to Power Supply (Huh)	366
7.3.5	Interbook Latchup Mechanisms – I/O to I/O Networks (Salcedo-Suner <i>et al.</i>)	367
7.3.6	System-Level Latchup	368
7.4	Circuit Solutions – Input Circuit	369
7.4.1	Latchup Prevention Circuit – Dual-Well ESD Networks	369
7.4.2	Latchup Prevention Circuit – Triple-Well ESD Networks	371
7.4.3	Sequence-Independent Input Networks	373
7.4.4	Sequence-Independent Input Networks: Off-Chip Drivers	373
7.4.5	Sequence-Independent Input Networks: ESD Networks	374
7.5	Power Supply Concepts	375
7.5.1	Power Supply Current Limit – Series Resistor	376
7.5.2	Power Supply Current Limit – Current Source	376
7.5.3	Power Supply Solutions – Voltage Regulator	378
7.5.4	Latchup Circuit Solutions – Power Supply Decoupling	378
7.6	Latchup Circuit Solutions – Power Supply to Power Supply Sequencing Circuitry	381
7.6.1	Power Supply to Power Supply Sequence-Independent Networks	382
7.6.2	Power Supply to Power Supply Control Circuits (Lin <i>et al.</i>)	383

xiv CONTENTS

7.7	Overshoot and Undershoot Clamp Networks	385
7.7.1	Passive Clamp Networks	385
7.7.2	Active Clamp Networks	387
7.7.3	Dynamic Threshold Triple-Well Passive and Active Clamp Networks	390
7.8	Passive and Active Guard Rings	391
7.8.1	Passive Guard Ring Circuits and Structures	392
7.8.2	Active Guard Ring Circuits and Structures	392
7.9	Triple-Well Noise and Latchup Suppression Structures	400
7.10	System-Level Issues	400
7.11	Summary and Closing Comments	401
	Problems	401
	References	402
Chapter 8 Latchup Computer Aided Design (CAD) Methods		407
8.1	Latchup CAD Rules	407
8.1.1	Fundamental Latchup Design Rules	408
8.1.2	Local Latchup Rules	408
8.1.3	Voltage Condition Rules	409
8.1.4	Off-Chip Driver Rules	409
8.1.5	Gate Array Design Rules	410
8.1.6	Mixed Voltage Applications and Special Circuits Rules	410
8.1.7	Global Chip Level Rules	411
8.1.8	External Latchup Design Rules	412
8.2	Design Rule Checking	413
8.2.1	Identification of Guard Rings	413
8.3	Computer-Aided Design Extraction	
	Methodologies – Searching for the pnpn	413
8.3.1	Extraction of the Parasitic pnpn Using Model Graphs (Li)	415
8.3.2	CAD Extraction Methodology (Zhan–Feng–Wu–Chen–Guan–Wang Method)	418
8.3.3	CAD Extraction Methodology – Extraction of the Parasitic pnpn (Habitz–Galland–Washburn Method)	419
8.4	CAD Extraction Methods – Searching for the Guard Rings	420
8.4.1	Virtual Design Level Methodology (Voldman–Sullivan–Nickel–Bass)	421
8.4.2	Built-in Guard Rings	421
8.4.3	Guard Ring Parameterized Cells (Pcell) (Voldman–Perez)	422
8.4.4	CAD Automation of Guard Ring Resistance	423
8.4.5	CAD Automation of Guard Ring Modification Methodology (Ker–Jiang–Peng–Shieh)	425
8.5	Latchup Extraction Methods and Tools	426
8.5.1	Latchup Extraction Tool (Ramaswamy–Sinha–Kadamati–Gharpurey Method)	426
8.5.2	CAD Verification – Design Error Detector Methodology (Venugopal–Sinha–Ramaswamy–Duvvury–Prasad–Raghu–Kadamati)	427
8.5.3	CAD Verification Methodology (Kimura–Tsujikawa)	428

8.5.4	CAD Design Methodology – Modification of Well and Substrate Contact Placement Based on Injection Source	429
8.5.5	Method of Well and Contact Spacing from External Source (Chatty-Brennan)	431
8.5.6	Method of Well and Contact Spacing for Array I/O	431
8.5.7	Transmission Probability Methodology (Voldman-Watson)	433
8.5.8	Global Placement Methodology (Voldman)	435
8.5.9	Method of Latchup, Placement and Routing Cosynthesis (Cohn-Basaran)	437
8.6	Latchup CAD Simulation	439
8.6.1	Latchup CAD Semiconductor Device Simulation	439
8.6.2	Latchup CAD Circuit Models	440
8.7	Summary and Closing Comments	440
	Problems	441
	References	441

Index	445
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